1N5819WT

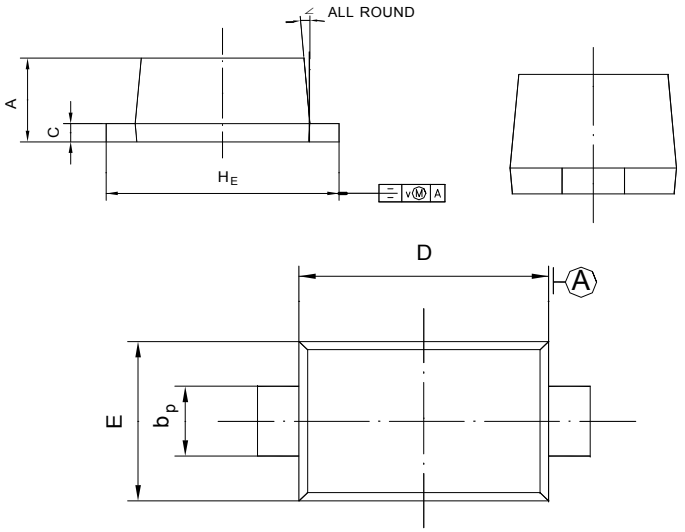
0.35 AMP SURFACE MOUNT SCHOTTKY BARRIER RECTIFIERS

FEATURES

- Metal silicon junction, majority carrier conduction
- Guarding for overvoltage protection
- Low power loss, high efficiency
- High current capability
- low forward voltage drop
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: SOD-523
- Terminals: Solderable per MIL-STD-750, Method 2026



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.50	0.40 0.20	0.14 0.05	1.30 1.10	0.90 0.75	1.70 1.50	0.1	5°

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Reverse Voltage	V_R	40	V
Average Forward Rectified Current	$I_{F(AV)}$	350	mA
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2	A
Power Dissipation	P_{tot}	200	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	°C

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Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at I_R=10uA	$V_{(BR)R}$	40	- - -	- - -	V
Reverse Leakage Current at V_R =30V	I_R	- -	- -	5	μA
Forward Voltage at I_F = 20 mA at I_F = 200 mA	V_F	- -	- -	0.37 0.6	V
Total Capacitance at V_R = 0 V, f = 1 MHz	C_T	-	50	-	pF
Reverse Recovery Time at I_F = I_R = 200 mA, I_{rr} = 0.1 I_R, R_L = 100 Ω	t_{rr}	-	10	-	ns

RATING AND CHARACTERISTIC CURVES (1N5819WT)

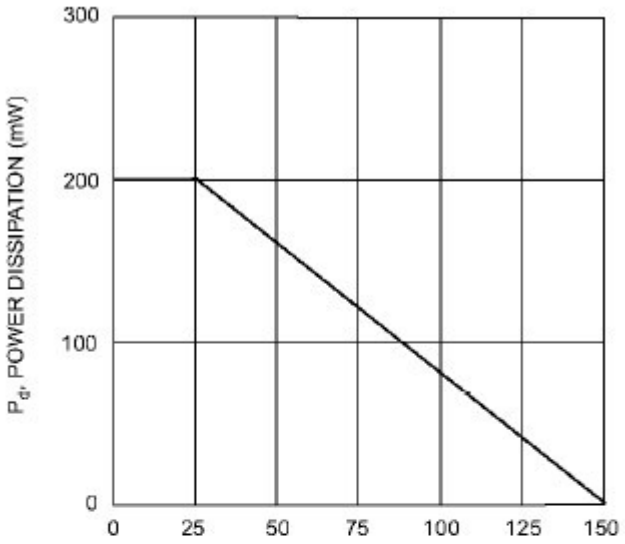

Fig. 1 Power Derating Curve

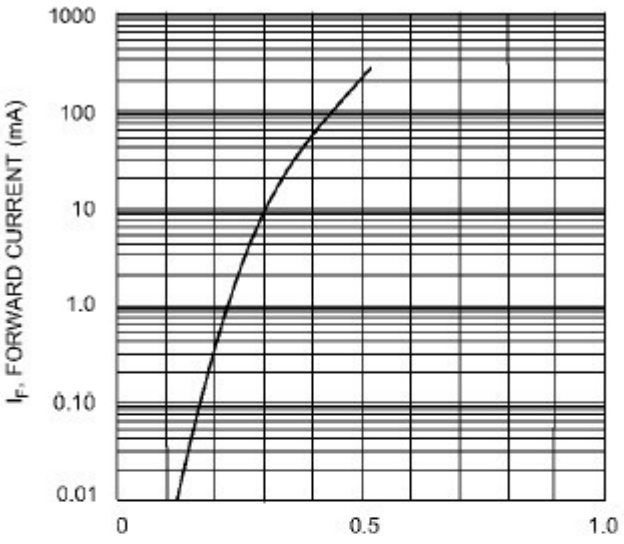

Fig. 2 Typical Forward Characteristics

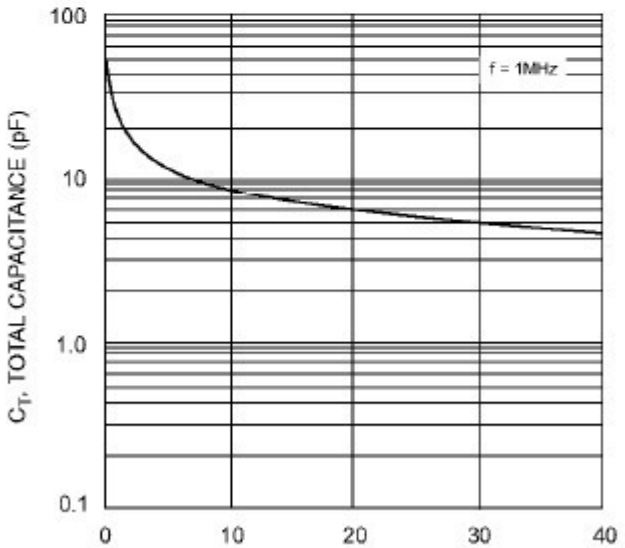

Fig. 3 Total Capacitance vs Reverse Voltage